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ALPHA & OMEGA SEMICONDUCTOR,  
LTD.  
ALPHA & OMEGA SEMICONDUCTOR,  
INC.

UNITED STATES DISTRICT COURT  
NORTHERN DISTRICT OF CALIFORNIA  
SAN FRANCISCO DIVISION

ALPHA & OMEGA SEMICONDUCTOR,  
LTD., a Bermuda corporation; and  
ALPHA & OMEGA SEMICONDUCTOR,  
INC., a California corporation,

Plaintiffs and Counterdefendants,

v.

FAIRCHILD SEMICONDUCTOR  
CORP., a Delaware corporation,

Defendant and Counterclaimant.

AND RELATED COUNTERCLAIMS.

TOWNSEND AND TOWNSEND AND  
CREW LLP  
ERIC P. JACOBS (SBN 88413)  
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Counterclaimant FAIRCHILD  
SEMICONDUCTOR CORPORATION

Case No. C 07-2638 JSW  
(Consolidated with Case No. C-07-2664 JSW)

**JOINT STIPULATION TO APPLY THE  
COURT'S CONSTRUCTION OF CERTAIN  
PHRASES TO OTHER SIMILAR  
PHRASES PURSUANT TO CIVIL L.R. 7-12**

Alpha and Omega Semiconductor, Ltd. and Alpha and Omega Semiconductor, Inc. (“AOS”) and Fairchild Semiconductor Corporation (“Fairchild”) (collectively, the “Parties”), pursuant to Civil Local Rule 7-12, hereby stipulate as follows:

WHEREAS the patents in dispute have multiple claims with similar claim language; and

WHEREAS the parties seek to limit the number of terms or phrases to be construed by the Court;

Pursuant to Civil L.R. 7-12, IT IS HEREBY STIPULATED by and between the Parties, through their respective counsel of record, that the Court’s construction of the phrases in the table below on the left will apply to the corresponding phrases below on the right, except that where the syntax of a phrase might cause the Court’s claim construction to fail to track the language of the phrase precisely, the parties agree that the core issue addressed by the claim construction shall nevertheless apply.

Phrase to be Construed by the Court	Phrase for which the Same Construction will Apply
wherein the heavy body forms an abrupt junction with the well ‘481 patent, claim 1	wherein the heavy body forms an abrupt junction with the well ‘481 patent, claim 6; ‘406 patent, claim 13  wherein the doped heavy body ... forms an abrupt junction with the well ‘481 patent, claim 15  the heavy body forming an abrupt junction with the well ‘406 patent, claim 1  the heavy body ... forming an abrupt junction with the well ‘195 patent, claim 1  to form an abrupt junction between the heavy body and the well ‘195 patent, claim 21
depth of the junction, relative to the depth of the well, is adjusted so that a	depth of the heavy body relative to a depth of the well is adjusted so that breakdown of the transistor

1 transistor breakdown initiation point is 2 spaced away from the trench in the 3 semiconductor, when voltage is applied 4 to the transistor 5 '481 patent, claim 1	originates in the semiconductor in a region spaced away from the trenches when voltage is applied to the transistor  '481 patent, claim 6; '406 patent, claim 13  depth of the heavy body junction relative to a maximum depth of the well, is adjusted so that a peak electric field in the substrate is spaced away from the trench when voltage is applied to the transistor  '481 patent, claim 15  location of the abrupt junction relative to the depth of the well is adjusted so that a transistor breakdown initiation point is spaced away from the trench in the semiconductor, when voltage is applied to the transistor  '406 patent, claim 1
11 acting as a field plate to extend the 12 device breakdown voltage in the 13 termination region 14 '947 patent, claim 1	acts as a field plate termination  '947 patent, claim 5  forming a field plate around the transistor regions  '947 patent, claim 6

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1 Dated: June 13, 2008

MORGAN, LEWIS & BOCKIUS LLP

2  
3 By /s/ Andrew J. Wu  
4 Andrew J. Wu

5 Attorneys for Plaintiffs and  
6 Counterdefendants  
7 ALPHA & OMEGA SEMICONDUCTOR,  
8 LTD. AND ALPHA & OMEGA  
9 SEMICONDUCTOR, INC.

10 Dated: June 13, 2008

TOWNSEND AND TOWNSEND AND  
CREW LLP

11 By /s/ Eric P. Jacobs  
12 Eric P. Jacobs

13 Attorneys for Defendant and  
14 Counterclaimant FAIRCHILD  
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**GENERAL ORDER ATTESTATION**

Pursuant to General Order No. 45, Section X(B) regarding signatures, I, Andrew J. Wu attest that concurrence in the filing of this document has been obtained from Eric P. Jacobs. I declare under penalty of perjury under the laws of the United States of America that the foregoing is true and correct. Executed this 13th day of June, 2008, at Pittsburgh, Pennsylvania.

/s/ Andrew J. Wu

Andrew J. Wu

**ORDER**

Pursuant to stipulation, IT IS SO ORDERED.

Dated: \_\_\_\_\_, 2008

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Hon. Jeffrey S. White  
United States District Judge